Avinash Patsha

List of Publications by Year in descending order

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Δυινίλομ Ράτομα

#	Article	IF	CITATIONS
1	Growth-Etch Metal–Organic Chemical Vapor Deposition Approach of WS ₂ Atomic Layers. ACS Nano, 2021, 15, 526-538.	14.6	56
2	Localized Charge Transfer Process and Surface Band Bending in Methane Sensing by GaN Nanowires. Journal of Physical Chemistry C, 2015, 119, 21251-21260.	3.1	35
3	Raman imaging on highâ€quality graphene grown by hotâ€filament chemical vapor deposition. Journal of Raman Spectroscopy, 2012, 43, 1864-1867.	2.5	29
4	Effect of substrate heating and microwave attenuation on the catalyst free growth and field emission of carbon nanotubes. Carbon, 2015, 94, 256-265.	10.3	27
5	Influence of oxygen in architecting large scale nonpolar GaN nanowires. Journal of Materials Chemistry C, 2013, 1, 8086.	5.5	22
6	Seeded-growth of WS ₂ atomic layers: the effect on chemical and optical properties. Nanoscale, 2019, 11, 22493-22503.	5.6	22
7	Direct Evidence of Mg Incorporation Pathway in Vapor–Liquid–Solid Grown p-type Nonpolar GaN Nanowires. Journal of Physical Chemistry C, 2014, 118, 24165-24172.	3.1	21
8	Probing Localized Surface Plasmons of Trisoctahedral Gold Nanocrystals for Surface Enhanced Raman Scattering. Journal of Physical Chemistry C, 2016, 120, 27003-27012.	3.1	19
9	Large-Scale characterization of Two-Dimensional Monolayer MoS2 Island Domains Using Spectroscopic Ellipsometry and Reflectometry. Applied Surface Science, 2020, 524, 146418.	6.1	18
10	Localized tip enhanced Raman spectroscopic study of impurity incorporated single GaN nanowire in the sub-diffraction limit. Applied Physics Letters, 2015, 107, .	3.3	15
11	Spectroscopic investigation of native defect induced electron–phonon coupling in GaN nanowires. Journal Physics D: Applied Physics, 2017, 50, 275103.	2.8	15
12	Optical Properties of Monodispersed AlGaN Nanowires in the Single-Prong Growth Mechanism. Crystal Growth and Design, 2015, 15, 1311-1318.	3.0	14
13	Polarized Tip-Enhanced Raman Spectroscopy in Understanding Metal-to-Insulator and Structural Phase Transition in VO ₂ . Journal of Physical Chemistry C, 2019, 123, 11189-11196.	3.1	14
14	Probing crystallographic orientation of a single GaN nanotube using polarized Raman imaging. Journal of Raman Spectroscopy, 2013, 44, 651-654.	2.5	13
15	Optically confined polarized resonance Raman studies in identifying crystalline orientation of sub-diffraction limited AlGaN nanostructure. Applied Physics Letters, 2015, 106, .	3.3	12
16	Effect of Scattering Efficiency in the Tip-Enhanced Raman Spectroscopic Imaging of Nanostructures in the Sub-diffraction Limit. Journal of Physical Chemistry C, 2017, 121, 26967-26975.	3.1	10
17	Size-Dependent Localized Phonon Population in Semiconducting Si Nanowires. Nano Letters, 2018, 18, 7181-7187.	9.1	9
18	Nonpolar <i>p</i> -GaN/ <i>n</i> -Si heterojunction diode characteristics: a comparison between ensemble and single nanowire devices. Journal Physics D: Applied Physics, 2015, 48, 395102.	2.8	8

Ανίναςη Ράτσηα

#	Article	IF	CITATIONS
19	Bright excitonic multiplexing mediated by dark exciton transition in two-dimensional TMDCs at room temperature. Materials Horizons, 2022, 9, 1089-1098.	12.2	8
20	Halide chemical vapor deposition of 2D semiconducting atomically-thin crystals: From self-seeded to epitaxial growth. Applied Materials Today, 2022, 26, 101379.	4.3	5
21	Nano-spectroscopic and nanoscopic imaging of single GaN nanowires in the sub-diffraction limit. Journal of Applied Physics, 2020, 127, 173103.	2.5	3
22	Effect of Ar+ implantation on the optical properties of Al/GaN nanowires. AIP Conference Proceedings, 2017, , .	0.4	2
23	Growth of GaN nanostructures on graphene. , 2011, , .		0
24	Catalysis free growth of GaN nanostructures. , 2012, , .		0
25	Self-catalyzed anisotropic growth of GaN spirals. , 2012, , .		0
26	Raman Spectral Mapping of III–V Nitride and Graphene Nanostructures. Mapan - Journal of Metrology Society of India, 2013, 28, 279-283.	1.5	0
27	Optical properties of Mg doped p-type GaN nanowires. AIP Conference Proceedings, 2015, , .	0.4	0